

NCE3080L

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3080L uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =30V,I_D =80A

 $R_{DS(ON)}$ <6.5m Ω @ V_{GS} =10V

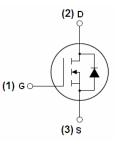
 $R_{DS(ON)}$ < 10m Ω @ V_{GS} =5V

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!



Schematic diagram



Marking and pin assignment



TO-251S top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3080L	NCE3080L	TO-251S	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	80	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	50	Α
Pulsed Drain Current	I _{DM}	170	Α
Maximum Power Dissipation	P _D	83	W
Derating factor		0.56	W /℃
Single pulse avalanche energy (Note 5)	E _{AS}	150	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$ C



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Thermal Characteristic

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics			•				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μΑ	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA 1		1.6	3	V	
Drain-Source On-State Resistance	Б	V _{GS} =10V, I _D =30A	-	5.5	6.5	- mΩ	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =5V, I _D =24A	-	7.5	10		
Forward Transconductance	g FS	V _{DS} =5V,I _D =24A	20	-	-	S	
Dynamic Characteristics (Note4)			•				
Input Capacitance	C _{lss}	\/ -45\/\/ -0\/	-	2330	-	PF	
Output Capacitance	C _{oss}	V_{DS} =15V, V_{GS} =0V, F=1.0MHz	-	460	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	230	-	PF	
Switching Characteristics (Note 4)			•				
Turn-on Delay Time	t _{d(on)}		-	20	-	nS	
Turn-on Rise Time	t _r	V _{DD} =10V,I _D =30A	-	15	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =2.7 Ω	-	60	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg	\/ -40\/ -20 \	-	51	-	nC	
Gate-Source Charge	Q _{gs}	V_{DS} =10V, I_{D} =30A, V_{GS} =10V	-	14	-	nC	
Gate-Drain Charge	Q _{gd}	VGS=10V	-	11	-	nC	
Drain-Source Diode Characteristics	·						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =24A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	80	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 80A	-	32	50	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs(Note3)	-	12	20	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

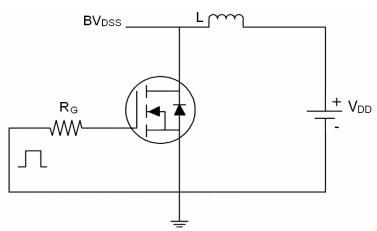
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=15V,V_G=10V,L=1mH,Rg=25 Ω

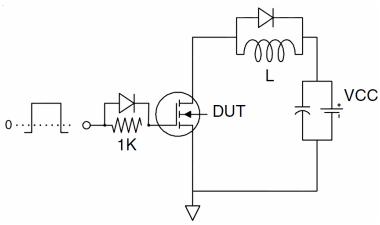


Test Circuit

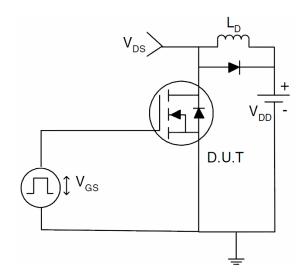
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit:





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Typical Electrical and Thermal Characteristics (Curves)

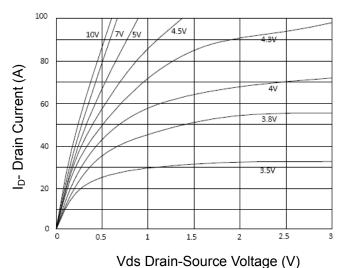


Figure 1 Output Characteristics

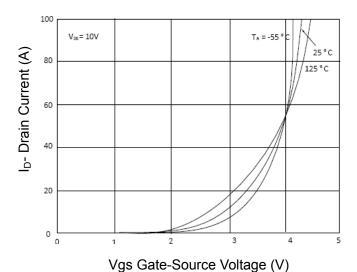


Figure 2 Transfer Characteristics

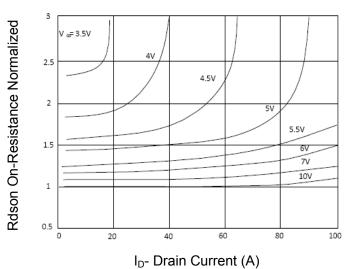


Figure 3 Rdson- Drain Current

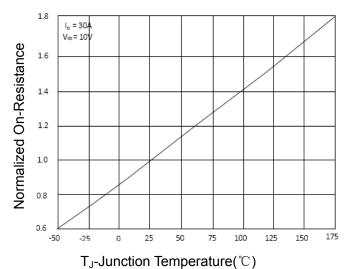


Figure 4 Rdson-Junction Temperature

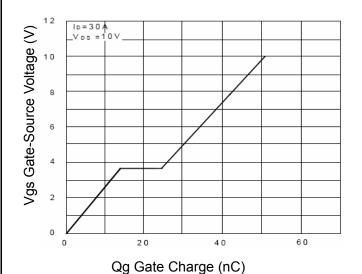


Figure 5 Gate Charge

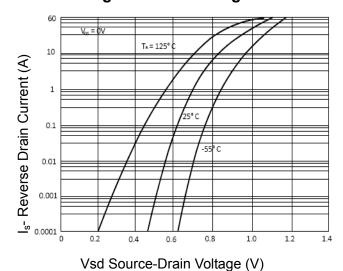
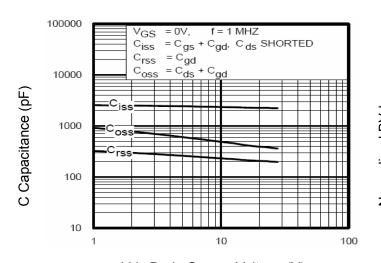


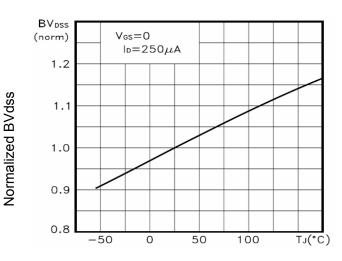
Figure 6 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



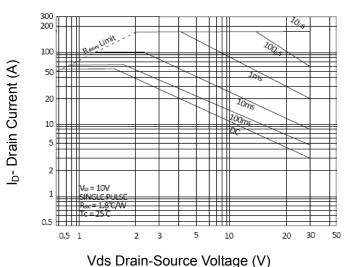
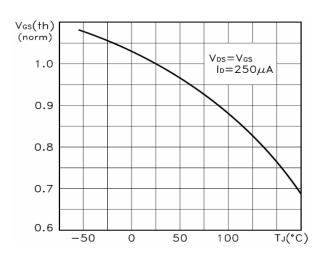


Figure 8 Safe Operation Area



T_J-Junction Temperature(°C)

Figure 10 V_{GS(th)} vs Junction Temperature

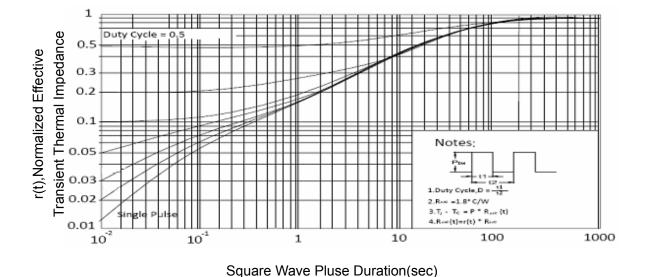
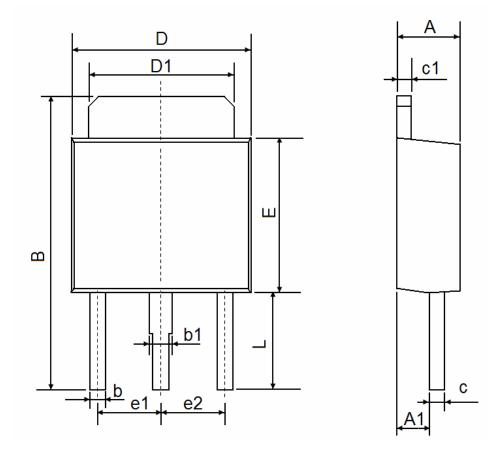


Figure 11 Normalized Maximum Transient Thermal Impedance

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TO-251S Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.250	2.350	0.089	0.093	
A1	1.150	1.250	0.045	0.049	
В	10.200	10.800	0.402	0.425	
b	0.550	0.650	0.022	0.026	
b1	0.750	0.850	0.030	0.033	
С	0.480	0.540	0.019	0.021	
c1	0.480	0.540	0.019	0.021	
D	6.400	6.600	0.252	0.260	
D1	5.250	5.350	0.207	0.211	
E	5.400	5.600	0.213	0.220	
e1	2.300 TYP		0.091 TYP		
e2	2.300 TYP		0.091 TYP		
L	3.300	3.700	0.130	0.146	



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